AMENDMENTS TO THE SPECIFICATION:

Please replace paragraph [0039] beginning at page 13, line 5, with the following rewritten paragraph:

[0039] In addition, it is contemplated that the temperature stability of switched variable capacitor 20, particularly in its minimum capacitance state (transistor 14 off) is greatly improved by this invention. The relation of junction capacitance C_j:

$$C_j \propto \frac{1}{\sqrt{V_R + V_{bi}}}$$

indicates that as reverse bias voltage V_R increases, the dependence of junction capacitance C_j on the built-in voltage V_{bi} decreases. The built-in voltage V_{bi} is dependent on temperature, while the reverse bias voltage V_R applied by bias transistors 18 can be regulated (by an on-chip voltage regulator, band-gap reference circuit, or the like) to be stable with temperature. As a result, an increase in the reverse bias voltage V_R can reduce the temperature sensitivity of junction capacitance C_j. Because bias transistors 18 can apply a stable, high magnitude, reverse bias voltage V_R to ~~across~~ the source/drain regions ~~junctions~~ of transistor 14, the junction capacitance C_j can therefore be made significantly more stable over temperature than according to conventional circuits. Stability of parasitic capacitance C_p' over temperature thus translates into temperature stability of the minimum capacitance C_{min}, which depends on parasitic capacitance C_p':

$$C_{min} = \frac{CC_p'}{2(C + C_p')}$$

The capacitance of switched variable capacitor 20 in the minimum capacitance state (transistor 14 off) is therefore rendered more stable by the present invention.